

## Silicon PNP Power Transistors

## 2SA1265N

## DESCRIPTION

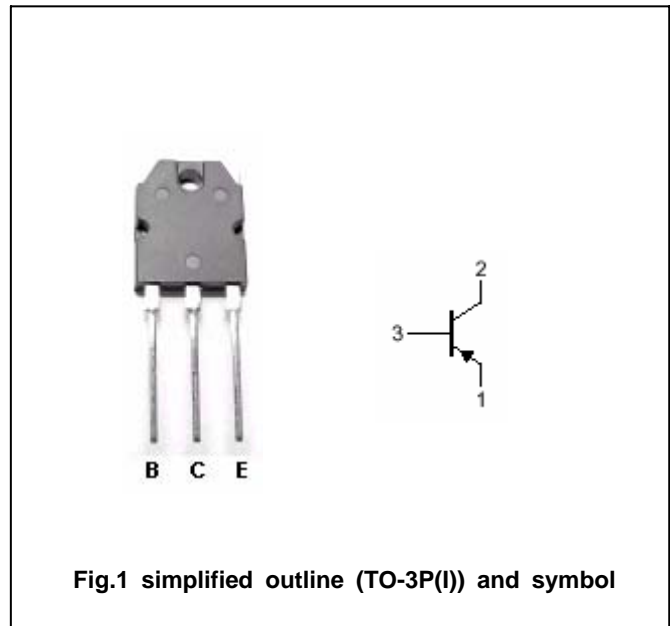
- With TO-3P(I) package
- Complement to type 2SC3182
- 2SA1265 with short pin

## APPLICATIONS

- Power amplifier applications

## PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings( $T_a=25^{\circ}\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-140	V
$V_{CEO}$	Collector-emitter voltage	Open base	-140	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-10	A
$I_B$	Base current		-1	A
$P_T$	Total power dissipation	$T_C=25^{\circ}\text{C}$	100	W
$T_j$	Junction temperature		150	$^{\circ}\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^{\circ}\text{C}$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-50mA, I <sub>B</sub> =0	-140			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-7A; I <sub>B</sub> =-0.7A		-0.8	-2.0	V
V <sub>BE</sub>	Base-emitter voltage	I <sub>C</sub> =-5A; V <sub>CE</sub> =-5V		-1.0	-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-140V; I <sub>E</sub> =0			-5	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-5	μ A
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-1A; V <sub>CE</sub> =-5V	55		160	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-5A; V <sub>CE</sub> =5V	35			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-1A; V <sub>CE</sub> =-5V		30		MHz
C <sub>ob</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =10V; f=1MHz		480		pF

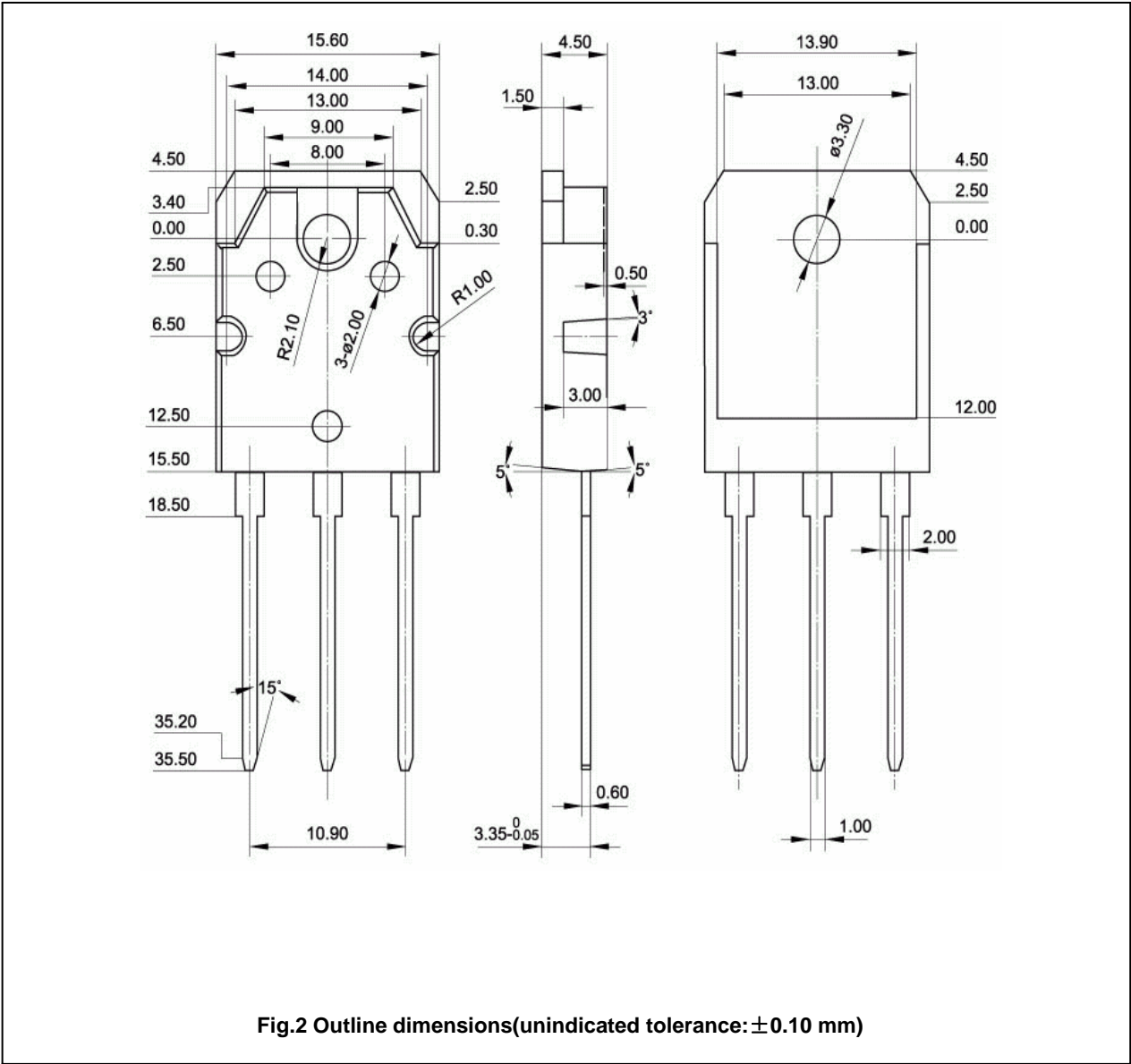
◆ h<sub>FE-1</sub> Classifications

R	O
55-110	80-160

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PACKAGE OUTLINE



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